Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

## 2SA1213

# Power Amplifier Applications Power Switching Applications

- Low saturation voltage:  $V_{CE (sat)} = -0.5 \text{ V (max) (I}_{C} = -1 \text{ A)}$
- High speed switching time:  $t_{stg} = 1.0 \mu s$  (typ.)
- Small flat package
- $P_C = 1.0$  to 2.0 W (mounted on ceramic substrate)
- Complementary to 2SC2873

#### **Maximum Ratings (Ta = 25°C)**

| Characteristics             | Symbol           | Rating     | Unit |  |
|-----------------------------|------------------|------------|------|--|
| Collector-base voltage      | $V_{CBO}$        | -50        | V    |  |
| Collector-emitter voltage   | V <sub>CEO</sub> | -50        | V    |  |
| Emitter-base voltage        | V <sub>EBO</sub> | <b>-</b> 5 | V    |  |
| Collector current           | Ic               | -2         | Α    |  |
| Base current                | Ι <sub>Β</sub>   | -0.4       | Α    |  |
|                             | P <sub>C</sub>   | 500        | mW   |  |
| Collector power dissipation | PC               | 1000       |      |  |
|                             | (Note 1)         | 1000       |      |  |
| Junction temperature        | Tj               | 150        | °C   |  |
| Storage temperature range   | T <sub>stg</sub> | −55 to 150 | °C   |  |

Note 1: Mounted on ceramic substrate (250 mm<sup>2</sup> × 0.8 t)

1.6MAX 4.6MAX 1.7MAX.  $0.4 \pm 0.05$ + 0.08 0.4 - 0.05 + 0.08 0.4 - 0.05 1.5 ± 0.1 1.5 ± 0.1 1. Base 2. Collector (heat sink) 3. Emitter PW-MINI **JEDEC** JEITA SC-62 TOSHIBA 2-5K1A

Weight: 0.05 g (typ.)

2SA1213

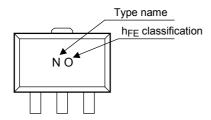


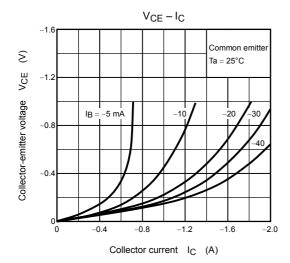
### Electrical Characteristics (Ta = 25°C)

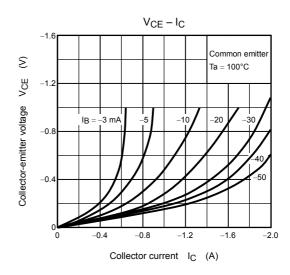
| Characteristics                     |                  | Symbol                          | Test Condition                                                                                                                                                       | Min | Тур. | Max  | Unit |
|-------------------------------------|------------------|---------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------|------|
| Collector cut-off current           |                  | I <sub>CBO</sub>                | $V_{CB} = -50 \text{ V}, I_E = 0$                                                                                                                                    | _   | _    | -0.1 | μΑ   |
| Emitter cut-off current             |                  | I <sub>EBO</sub>                | $V_{EB} = -5 \text{ V}, I_C = 0$                                                                                                                                     | _   | _    | -0.1 | μA   |
| Collector-emitter breakdown voltage |                  | V (BR) CEO                      | I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0                                                                                                                          | -50 | _    | _    | V    |
| DC current gain                     |                  | h <sub>FE (1)</sub><br>(Note 2) | V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A                                                                                                                      | 70  | _    | 240  |      |
|                                     |                  | h <sub>FE (2)</sub>             | V <sub>CE</sub> = -2 V, I <sub>C</sub> = -2.0 A                                                                                                                      | 20  | _    | _    |      |
| Collector-emitter sa                | turation voltage | V <sub>CE (sat)</sub>           | I <sub>C</sub> = -1 A, I <sub>B</sub> = -0.05 A                                                                                                                      | _   | _    | -0.5 | V    |
| Base-emitter saturation voltage     |                  | V <sub>BE (sat)</sub>           | I <sub>C</sub> = -1 A, I <sub>B</sub> = -0.05 A                                                                                                                      | _   | _    | -1.2 | V    |
| Transition frequency                |                  | f <sub>T</sub>                  | V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A                                                                                                                      | _   | 120  | _    | MHz  |
| Collector output capacitance        |                  | C <sub>ob</sub>                 | V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz                                                                                                               | _   | 40   | _    | pF   |
| Switching time                      | Turn-on time     | t <sub>on</sub>                 | I <sub>B1</sub> OUTPUT<br>I <sub>B1</sub> OUTPUT<br>G<br>INPUT I <sub>B1</sub> OUTPUT<br>G<br>INPUT I <sub>B1</sub> OUTPUT<br>G<br>G<br>INPUT I <sub>B1</sub> OUTPUT | _   | 0.1  | _    |      |
|                                     | Storage time     | t <sub>stg</sub>                |                                                                                                                                                                      | _   | 1.0  | _    | μs   |
|                                     | Fall time        | t <sub>f</sub>                  | -I <sub>B1</sub> = I <sub>B2</sub> = 0.05 A,<br>DUTY CYCLE ≤ 1%                                                                                                      | _   | 0.1  | _    |      |

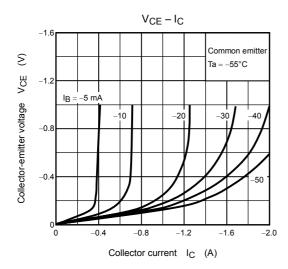
Note 2:  $h_{FE\ (1)}$  classification O: 70 to 140, Y: 120 to 240

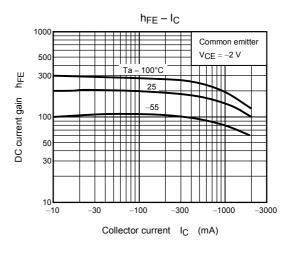
## Marking

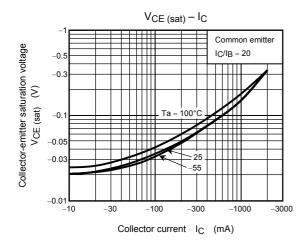


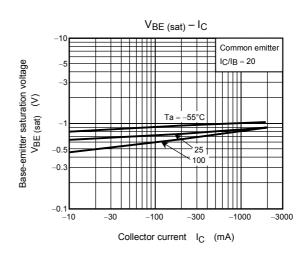




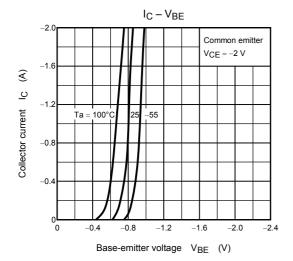


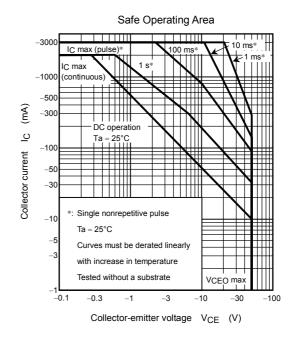


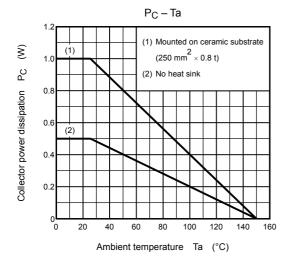




3







4 2002-08-19

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5

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